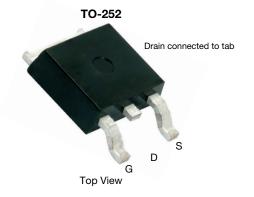


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Automotive N-Channel 150 V (D-S) 175 °C MOSFET

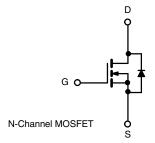
PRODUCT SUMMARY				
V _{DS} (V)	150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.052			
I _D (A)	25			
Configuration	Single			
Package	TO-252			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATING	GS (T _C = 25 °C, unle	ss otherwise noted	i)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	I-	25	
Continuous Drain Current	T _C = 125 °C	- I _D	16	
Continuous Source Current (Diode Conduc	ction) ^a	I _S	50	Α
Pulsed Drain Current ^b		I _{DM}	63	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	30	
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	45	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	107	W
	T _C = 125 °C] ' ^{'D}	35	, vv
Operating Junction and Storage Temperate	ure Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).



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SPECIFICATIONS ($T_C = 25$ °C,	unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3	4	ľ
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 150 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 150 V, T _J = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 150 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 15 A	-	0.038	0.052	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.104	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.136	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	33	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			1	1760	2200	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	ı	215	270	рF
Reverse Transfer Capacitance	C _{rss}			1	97	125	
Total Gate Charge ^c	Q_g			ı	34	51	
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 75 \text{ V}, I_{D} = 25 \text{ A}$	-	14.5	-	nC
Gate-Drain Charge ^c	Q_{gd}			1	5.4	-	
Gate Resistance	R_g		f = 1 MHz		1.0	3.2	Ω
Turn-On Delay Time ^c	t _{d(on)}				11	17	
Rise Time ^c	t _r	V_{DD} = 75 V, R_L = 3 Ω $I_D \cong$ 25 A, V_{GEN} = 10 V, R_g = 1 Ω		-	21	33	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	20	30	
Fall Time ^c	t _f			ı	12	20	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-		63	Α
Forward Voltage	V _{SD}	I _F =	= 20 A, V _{GS} = 0 V	-	0.87	1.5	V

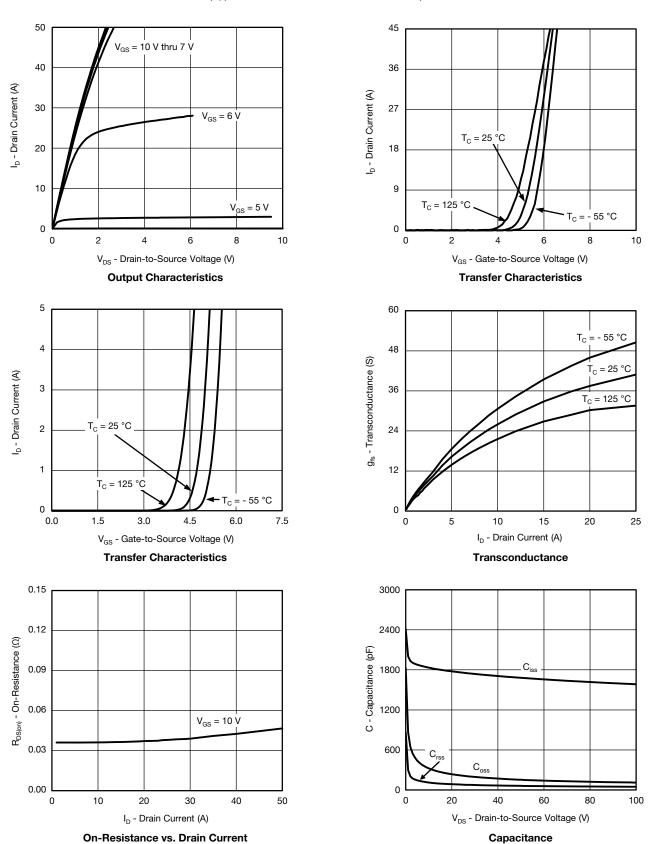
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

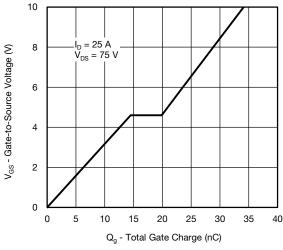


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

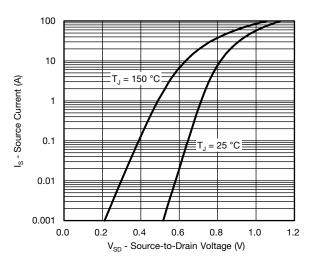




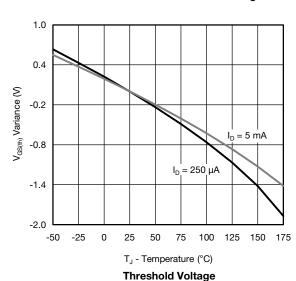
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

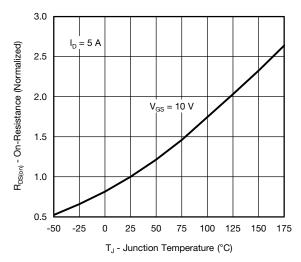


Gate Charge

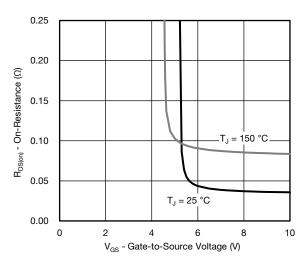


Source Drain Diode Forward Voltage

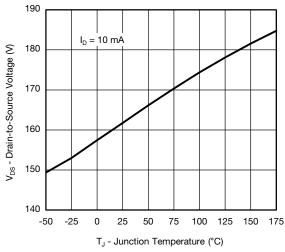




On-Resistance vs. Junction Temperature



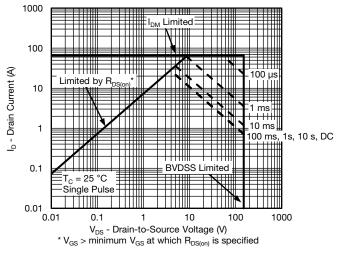
On-Resistance vs. Gate-to-Source Voltage



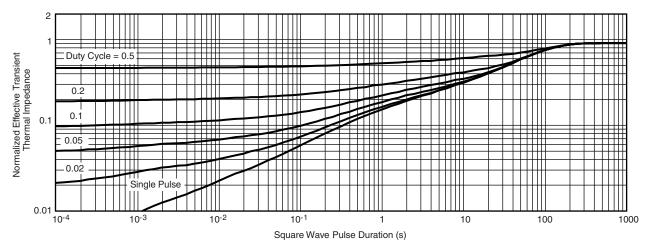
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



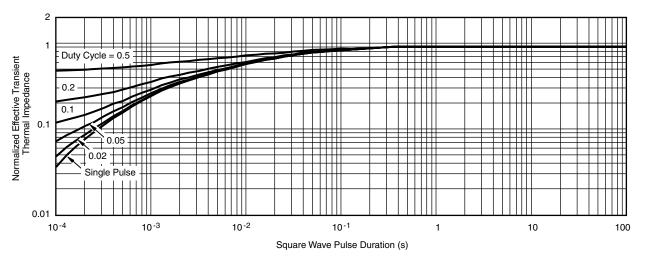
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to- Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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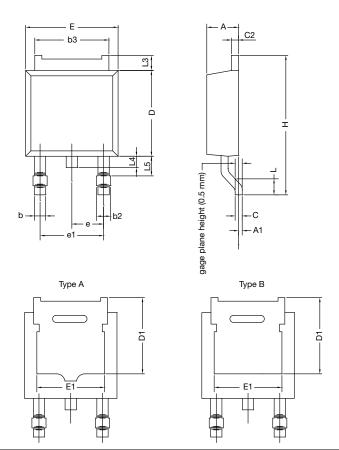
REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
G	08-Aug-15	R _g , C _{rss} , t _r and t _f changed

Note

a. As of April 2014



TO-252AA Case Outline



DIM.	MILLIN	METERS	INCHES	
	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	=
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	=
Н	9.40	10.41	0.370	0.410
е	2.28	BSC	0.090	BSC
e1	4.56	BSC	0.180	BSC
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

ECN: T24-0298-Rev. B, 29-Jul-2024 DWG: 6019

Notes

- Dimension L3 is for reference only
- Dimension D1 and E1 on type A and B is the same

Revision: 29-Jul-2024 1 Document Number: 64424



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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